

Amir Muhammad Afzal

List of Publications by Year in descending order

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Version: 2024-02-01

19
papers

526
citations

759233

12
h-index

794594

19
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19
all docs

19
docs citations

19
times ranked

557
citing authors

#	ARTICLE	IF	CITATIONS
1	High performance and gate-controlled GeSe/HfS ₂ negative differential resistance device. RSC Advances, 2022, 12, 1278-1286.	3.6	9
2	Ultrasensitive V doped WO ₃ 1D nanorods heterojunction photodetector with pronounced photosensing activities. Journal of Alloys and Compounds, 2022, 909, 164753.	5.5	5
3	Enhancing the electronic properties of the graphene-based field-effect transistor via chemical doping of KBr. Journal of Materials Science: Materials in Electronics, 2022, 33, 12416-12425.	2.2	3
4	Fast and high photoresponsivity gallium telluride/hafnium selenide van der Waals heterostructure photodiode. Journal of Materials Chemistry C, 2021, 9, 7110-7118.	5.5	10
5	A comparative study of electrical and opto-electrical properties of a few-layer p-WSe ₂ /n-WS ₂ heterojunction diode on SiO ₂ and h-BN substrates. RSC Advances, 2021, 11, 17901-17909.	3.6	6
6	Oxygen vacancies induced room temperature ferromagnetism and enhanced dielectric properties in Co and Mn co-doped ZnO nanoparticles. Journal of Materials Science: Materials in Electronics, 2021, 32, 9463-9474.	2.2	28
7	Highly Sensitive, Ultrafast, and Broadband Photo-Detecting Field-Effect Transistor with Transition-Metal Dichalcogenide van der Waals Heterostructures of MoTe ₂ and PdSe ₂ . Advanced Science, 2021, 8, e2003713.	11.2	65
8	p-GeSe/n-ReS ₂ Heterojunction Rectifier Exhibiting A Fast Photoresponse with Ultra-High Frequency Switching Applications. Advanced Materials Interfaces, 2021, 8, 2100705.	3.7	29
9	Ultrafast and Highly Stable Photodetectors Based on p-GeSe/n-ReSe ₂ Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 47882-47894.	8.0	26
10	Tunneling-based rectification and photoresponsivity in black phosphorus/hexagonal boron nitride/rhenium diselenide van der Waals heterojunction diode. Nanoscale, 2020, 12, 3455-3468.	5.6	40
11	Ultraviolet-light-driven current modulation of Au/WS ₂ /Gr Schottky barrier. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 117, 113837.	2.7	6
12	WS ₂ /GeSe/WS ₂ Bipolar Transistor-Based Chemical Sensor with Fast Response and Recovery Times. ACS Applied Materials & Interfaces, 2020, 12, 39524-39532.	8.0	48
13	High-Performance p-BP/n-PdSe ₂ Near-Infrared Photodiodes with a Fast and Gate-Tunable Photoresponse. ACS Applied Materials & Interfaces, 2020, 12, 19625-19634.	8.0	67
14	Multifunctional and high-performance GeSe/PdSe ₂ heterostructure device with a fast photoresponse. Journal of Materials Chemistry C, 2020, 8, 4743-4753.	5.5	47
15	Lamellar shape lead tungstate (PbWO ₄) nanostructures as synergistic catalyst for peroxidase mimetic activity. Materials Research Express, 2020, 7, 015520.	1.6	7
16	Formation of an MoTe ₂ based Schottky junction employing ultra-low and high resistive metal contacts. RSC Advances, 2019, 9, 10017-10023.	3.6	27
17	Gate Modulation of the Spin-orbit Interaction in Bilayer Graphene Encapsulated by WS ₂ films. Scientific Reports, 2018, 8, 3412.	3.3	20
18	Temperature-Dependent and Gate-Tunable Rectification in a Black Phosphorus/WS ₂ van der Waals Heterojunction Diode. ACS Applied Materials & Interfaces, 2018, 10, 13150-13157.	8.0	61

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19	Gate Tunable Transport in Graphene/MoS ₂ /(Cr/Au) Vertical Field-Effect Transistors. <i>Nanomaterials</i> , 2018, 8, 14.	4.1	22